AMENDMENTS TO THE CLAIMS

1. (Currently amended) A method of polishing and then cleaning substrates, comprising:

polishing a first substrate by pressing said first substrate against a first polishing surface; then

primarily cleaning said first substrate in a first of two first cleaning units; then secondarily cleaning said first substrate in a common second cleaning unit while supporting said first substrate on a table;

polishing a second substrate by pressing said second substrate against a second polishing surface; then

primarily cleaning said second substrate in a second of said two first cleaning units; and then

secondarily cleaning said second substrate in said common second cleaning unit while supporting said second substrate on said table.

wherein primarily cleaning said first substrate in said first of said two cleaning units
comprises primarily cleaning said first substrate in said first of said two cleaning units for a time
period that is greater than a time period for which said first substrate is secondarily cleaned in
said common cleaning unit, and

wherein primarily cleaning said second substrate in said second of said two cleaning units comprises primarily cleaning said second substrate in said second of said two cleaning units for a time period that is greater than a time period for which said second substrate is secondarily cleaned in said common cleaning unit.

Claims 2-9. (Canceled)

10. (Currently amended) The method according to claim1, wherein primarily cleaning said first substrate in said first of said two first cleaning units comprises cleaning said first substrate in said first of said two first cleaning units by subjecting said first substrate to a first cleaning function, and

primarily cleaning said second substrate in said second of said two first cleaning units comprises cleaning said second substrate in said second of said two first cleaning units by subjecting said second substrate to a second cleaning function that is the same as said first cleaning function.

- 11. (Previously presented) The method according to claim 1, further comprising:
 drying said first substrate and said second substrate after secondarily cleaning said first substrate and said second substrate.
- 12. (Previously presented) The method according to claim 1, wherein primarily cleaning said first substrate and said second substrate comprises supplying an etching liquid to said first substrate and said second substrate, or

secondarily cleaning said first substrate and said second substrate comprises supplying an etching liquid to said first substrate and said second substrate.

Claim 13. (Canceled)

14. (Previously presented) The method according to claim 1, wherein primarily cleaning said first substrate and said second substrate comprises using ionic water, ozone water, or hydrogenated water as a cleaning liquid, or

secondarily cleaning said first substrate and said second substrate comprises using ionic water, ozone water, or hydrogenated water as a cleaning liquid.

15. (Previously presented) The method according to claim1, wherein primarily cleaning said first substrate and primarily cleaning said second substrate comprises primarily cleaning said first substrate in parallel with primarily cleaning said second substrate.

Claims 16-21. (Canceled)

- 22. (Previously presented) The method according to claim 1, wherein polishing said first substrate and polishing said second substrate comprises polishing said first substrate in parallel with polishing said second substrate.
 - 23. (Previously presented) The method according to claim 1, further comprising: not pressing said first substrate against said second polishing surface.
 - 24. (Currently amended) The method according to claim 23, further comprising: not cleaning said first substrate in said second of said two first cleaning units.
 - 25. (Previously presented) The method according to claim 24, further comprising: not pressing said second substrate against said first polishing surface.
 - 26. (Currently amended) The method according to claim 25, further comprising: not cleaning said second substrate in said first of said two first cleaning units.
- 27. (Currently amended) The method according to claim 23, wherein primarily cleaning said first substrate in said first of said two first cleaning units comprises cleaning said first substrate in said first of said two first cleaning units by subjecting said first substrate to a first cleaning function, and

primarily cleaning said second substrate in said second of said two first cleaning units comprises cleaning said second substrate in said second of said two first cleaning units by subjecting said second substrate to a second cleaning function that is the same as said first cleaning function.

- 28. (Previously presented) The method according to claim 23, further comprising: drying said first substrate and said second substrate after secondarily cleaning said first substrate and said second substrate.
- 29. (Previously presented) The method according to claim 23, wherein primarily cleaning said first substrate and said second substrate comprises supplying an etching liquid to said first substrate and said second substrate, or

secondarily cleaning said first substrate and said second substrate comprises supplying an etching liquid to said first substrate and said second substrate.

Claim 30. (Canceled)

31. (Previously presented) The method according to claim 23, wherein primarily cleaning said first substrate and said second substrate comprises using ionic water, ozone water, or hydrogenated water as a cleaning liquid, or

secondarily cleaning said first substrate and said second substrate comprises using ionic water, ozone water, or hydrogenated water as a cleaning liquid.

32. (Previously presented) The method according to claim 23, wherein primarily cleaning said first substrate and primarily cleaning said second substrate comprises primarily cleaning said first substrate in parallel with primarily cleaning said second substrate.

- 33. (Previously presented) The method according to claim 1, further comprising: not cleaning said first substrate in said second of said two first cleaning units.
- 34. (Currently amended) The method according to claim 1, wherein secondarily cleaning said first substrate comprises supplying water to said first substrate while said first substrate is rotated via rotation of said a table, while supporting said first substrate, and

secondarily cleaning said second substrate comprises supplying water to said second substrate while said second substrate is rotated via rotation of said table, while supporting said second substrate.